



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

H5551

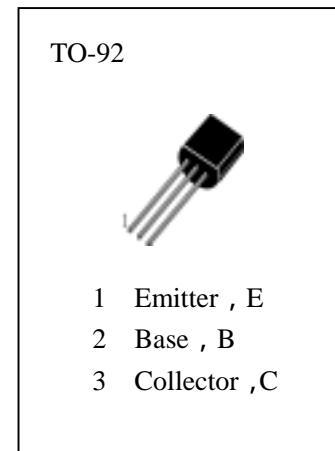
AMPLIFIER TRANSISTOR

Collector-Emitter Voltage: $V_{CEO}=160V$.

CollectorDissipation: $P_C(max)=625mW$

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg} —Storage Temperature.....	-55~150
T_j —Junction Temperature.....	150
P_C —Collector Dissipation.....	625mW
V_{CBO} —Collector-Base Voltage.....	180V
V_{CEO} —Collector-Emitter Voltage.....	160V
V_{EBO} —Emitter-Base Voltage.....	6V
I_C —Collector Current.....	600mA



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	180			V	$I_C=100 \mu A, I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	160			V	$I_C=1mA, I_B=0$
BV_{EBO}	Emitter-Base Breakdown Voltage	6			V	$I_E=10 \mu A, I_C=0$
I_{CBO}	Collector Cut-off Current			50	nA	$V_{CB}=120V, I_E=0$
I_{EBO}	Emitter-Base Cut-off Current			50	nA	$V_{EB}=4V, I_C=0$
$HFE(1)$	DC Current Gain	80				$V_{CE}=5V, I_C=1mA$
$HFE(2)$		80		280		$V_{CE}=5V, I_C=10mA$
$HFE(3)$		30				$V_{CE}=5V, I_C=50mA$
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage			0.15	V	$I_C=10mA, I_B=-1mA$
$V_{CE(sat2)}$				0.2	V	$I_C=50mA, I_B=5mA$
$V_{BE(sat1)}$	Base-Emitter Saturation Voltage			1	V	$I_C=10mA, I_B=1mA$
$V_{BE(sat2)}$				1	V	$I_C=50mA, I_B=5mA$
f_T	Current Gain-Bandwidth Product	100		300	MHz	$V_{CE}=10V, I_C=10mA$ $F=100MHz$